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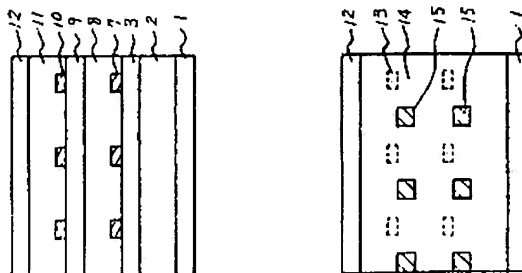
**PATENT ABSTRACTS OF JAPAN**(21) Application number: **61301248**(51) Intl. Cl.: **H01L 21/20 H01L 21/203 H01L 21/225  
H01S 3/18**(22) Application date: **19.12.86**

<p>(30) Priority:</p> <p>(43) Date of application publication: <b>28.06.88</b></p> <p>(84) Designated contracting states:</p>	<p>(71) Applicant: <b>HITACHI LTD</b></p> <p>(72) Inventor: <b>FUKUZAWA TADASHI</b></p> <p>(74) Representative:</p>
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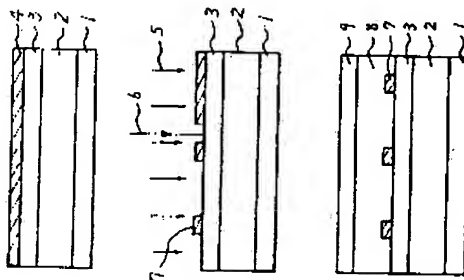
**(54) MANUFACTURE OF SEMICONDUCTOR FINE STRUCTURE**

(57) Abstract:

**PURPOSE:** To easily manufacture many quantum fine structures by etching Si grown in a single quantum well structure in an arbitrary shape, further growing a semiconductor crystal, then heat treating it to diffuse Si, and partly deleting a semiconductor hetero boundary.



**CONSTITUTION:** A GaAs quantum well layer 3 is grown on the barrier layer 2 of a substrate 1. Then, an Si epitaxial layer 4 is grown. A wafer is fed to an etching chamber, an electron beam 6 is irradiated in an XeF<sub>2</sub> gas, and Si- etched to obtain the remaining pattern 7 of the Si. It is again returned to the single crystal growing chamber, and a barrier layer 8 and a GaAs quantum well layer 9 are grown. Then, the Si is grown, an Si stripe 10 is formed, and a barrier layer 11 and a cap layer 12 are grown. Then, a heat treatment is conducted, and with an Si stripe 13 as a diffusion source the Si is diffused in the quantum well and the barrier layer. The mixed crystal 14 of the quantum well and the barrier layer is formed at a hetero boundary in which the Si is diffused. A buried hetero structure is obtained in a region 15 in which the Si is not diffused.



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